

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 01-290221

(43)Date of publication of application : 22.11.1989

(51)Int.Cl.

H01L 21/205

(21)Application number : 63-120872

(71)Applicant : FUJITSU LTD

(22)Date of filing : 18.05.1988

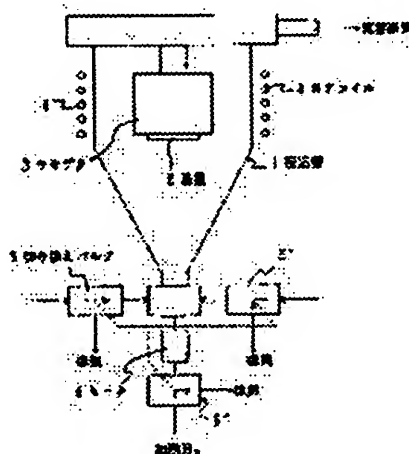
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(54) SEMICONDUCTOR VAPOR GROWTH METHOD

(57)Abstract:

PURPOSE: To execute epitaxy of an atomic layer of a compound semiconductor at a low temperature by a method wherein an alkyl compound is supplied to the crystal surface of a substrate, heated hydrogen is supplied to the surface of the substrate and a raw material gas of another element constituting the compound semiconductor is supplied to the surface of the substrate.

CONSTITUTION: In a vapor growth epitaxial growth method of a compound semiconductor, e.g., a typical; III to V compound, an alkyl metal as a raw material of a group III element is supplied to the crystal surface of a substrate 2; in a state that this alkyl metal has been adsorbed to the surface of the substrate 2, heated hydrogen is supplied and the alkyl metal in an adsorbed state is decomposed; a group III element layer is deposited; a raw material gas of a group V element is supplied. These raw material gases are introduced alternately into a reaction tube 1 by an operation of changeover valves 5, 5'. Although a temperature of heated hydrogen gas used for this treatment depends on an apparatus and a treatment condition, a substrate temperature + (300 to 800° C) is suitable. By this setup, even when the substrate temperature is lowered, a self-layer limiting effect can be obtained surely, while epitaxy of an atomic layer can be executed easily.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]